Form PTO 1449 (Rev. 2-32) U.S. Department of Commerce Patent and Trademark Office						Atty. Docket No. 034299-617		Serial No. 10/520,647					
Information Disclosure Statement by Applicant							Applicant: Marie D'Angelo, et al.						
(Use several sheets if necessary)						Filed: Ja	Filed: January 5, 2005		Group: (to be assigned)				
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